SGS-THOMSON MICROELECTRONICS

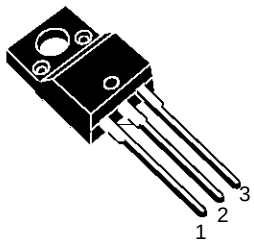
STP6NA60FP

N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP6NA60FP	600 V	< 1.2 Ω	3.9 A

- TYPICAL $R_{DS(on)}$ = 1 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD



TO-220FP

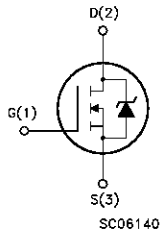
DESCRIPTION

This series of POWER MOSFETS represents the most advanced high voltage technology. The optmized cell layout coupled with a new proprietary edge termination concur to give the device low RDS(on) and gate charge, unequalled ruggedness and superior switching performance.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate-source Voltage	± 30	V
I_D	Drain Current (continuous) at T_c = 25 °C	3.9	A
I_D	Drain Current (continuous) at T_c = 100 °C	2.6	A
I_{DM}(•)	Drain Current (pulsed)	26	A
P_{tot}	Total Dissipation at T_c = 25 °C	40	W
	Derating Factor	0.32	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	2000	V
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	3.12	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	62.5	oC/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.5	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	6.5	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	215	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$) Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating $T_c = 100\ ^oC$			25 250	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$V $I_D = 2.5$ A		1	1.2	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	6.5			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 3$ A	3.5	5.6		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance ReverseTransfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		1150 155 40	1550 210 55	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 300 V I_D = 3 A R_G = 47 Ω V_{GS} = 10 V		35 90	55 125	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 480 V I_D = 3 A V_{GS} = 10 V		54 8 23	75	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 480 V I_D = 6 A R_G = 47 Ω V_{GS} = 10 V (see test circuit, figure 5)		80 20 115	110 30 155	ns ns ns

SOURCE DRAIN DIODE

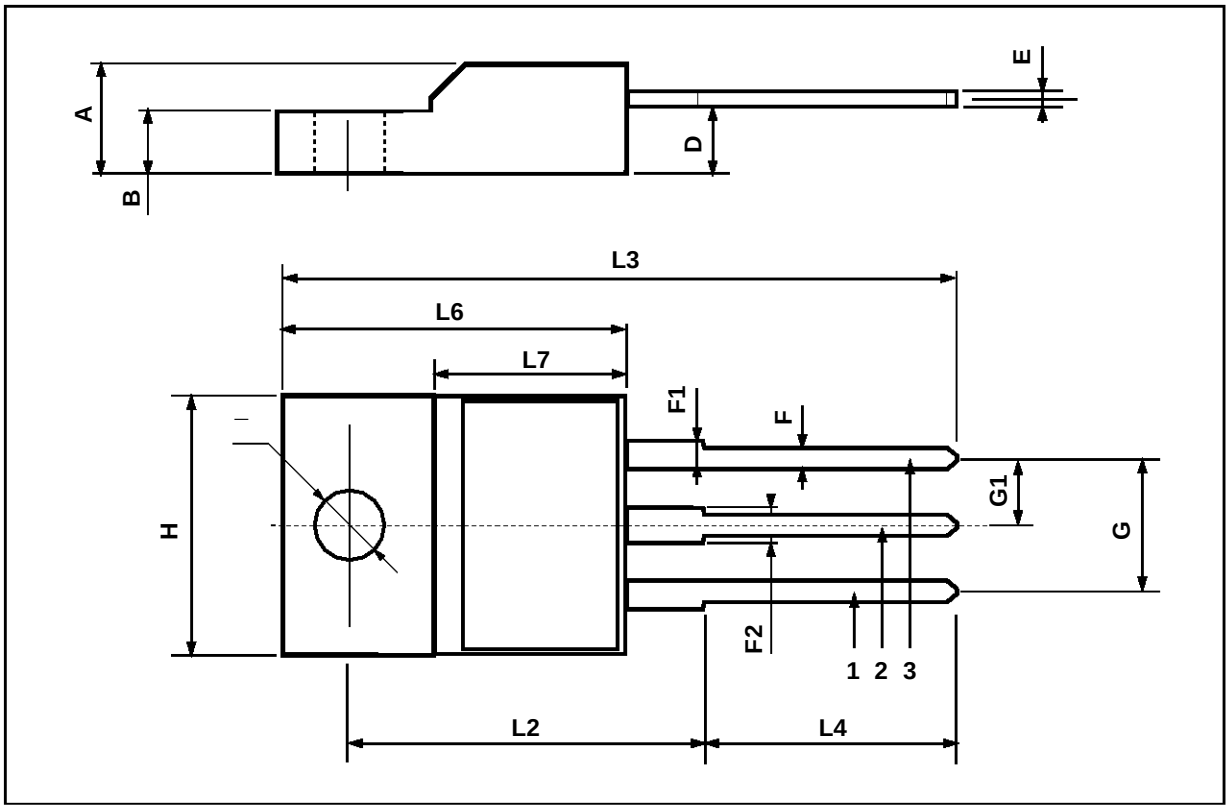
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				6.5 26	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 6.5 A V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 6 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		600		ns
Q_{rr}	Reverse Recovery Charge	(see circuit, figure 5)		9		µC
I_{RRM}	Reverse Recovery Current			30		A

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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